Low-Voltage CMOS Octal Transparent Latch Flow Through Pinout

With 5 V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX573 is a high performance, non–inverting octal transparent latch operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A $V_{\rm I}$ specification of 5.5 V allows MC74LCX573 inputs to be safely driven from 5.0 V devices.

The MC74LCX573 contains 8 D-type latches with 3-state standard outputs. When the Latch Enable (LE) input is HIGH, data on the Dn inputs enters the latches. In this condition, the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW, the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The 3-state standard outputs are controlled by the Output Enable (\overline{OE}) input. When \overline{OE} is LOW, the standard outputs are enabled. When \overline{OE} is HIGH, the standard outputs are in the high impedance state, but this does not interfere with new data entering into the latches. The LCX573 flow through design facilitates easy PC board layout.

Features

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5.0 V Tolerant Interface Capability With 5.0 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 \text{ V}$
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 μA)
 Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance:
 - ♦ Human Body Model >2000 V
 - ♦ Machine Model >200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

1



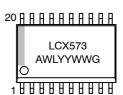
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS

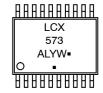


SOIC-20 WB DW SUFFIX CASE 751D





TSSOP-20 DT SUFFIX CASE 948E



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

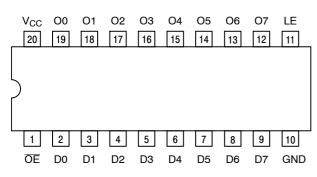


Figure 1. Pinout (Top View)

PIN NAMES

Pins	Function	
ŌĒ	Output Enable Input	
LE	Latch Enable Input	
D0-D7	Data Inputs	
00-07	3-State Latch Outputs	

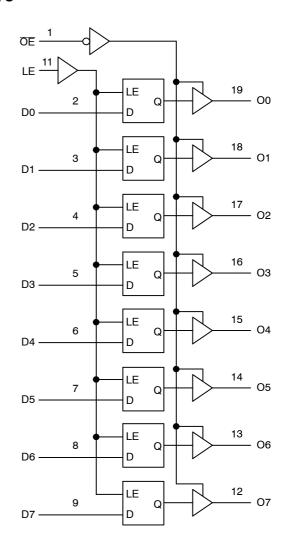


Figure 2. Logic Diagram

TRUTH TABLE

	Inputs		Inputs		Outputs	
ŌĒ	LE	Dn	On	Operating Mode		
L L	H H	ΗL	H L	Transparent (Latch Disabled); Read Latch		
L L	L L	h I	H L	Latched (Latch Enabled) Read Latch		
L	L	Х	NC	Hold; Read Latch		
Н	L	Х	Z	Hold; Disabled Outputs		
H H	H H	H L	Z Z	Transparent (Latch Disabled); Disabled Outputs		
H H	L L	h I	Z Z	Latched (Latch Enabled); Disabled Outputs		

H = High Voltage Level;

h = High Voltage Level One Setup Time Prior to the Latch Enable High-to-Low Transition

L = Low Voltage Level

I = Low Voltage Level One Setup Time Prior to the Latch Enable High-to-Low Transition

NC = No Change, State Prior to the Latch Enable High-to-Low Transition

X = High or Low Voltage Level or Transitions are Acceptable

Z = High Impedance State

For I_{CC} Reasons DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Units
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_{I} \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le +7.0$	Output in 3-State	V
		$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
Io	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C
MSL	Moisture Sensitivity		Level 1	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V _{CC}	Supply Voltage Operating Data Retention Only	2.0 1.5	2.5, 3.3 2.5, 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
V _O	Output Voltage (HIGH or LOW State) (3-State)	0		V _{CC} 5.5	V
I _{OH}	HIGH Level Output Current V _{CC} = 3.0 V - 3.6 V V _{CC} = 2.7 V - 3.0 V V _{CC} = 2.3 V - 2.7 V			-24 -12 -8	mA
l _{OL}	LOW Level Output Current $V_{CC} = 3.0 \text{ V} - 3.6 \text{ V}$ $V_{CC} = 2.7 \text{ V} - 3.0 \text{ V}$ $V_{CC} = 2.3 \text{ V} - 2.7 \text{ V}$			+24 +12 +8	mA
T _A	Operating Free-Air Temperature	-55		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V _{IN} from 0.8 V to 2.0 V, V _{CC} = 3.0 V	0		10	ns/V

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LCX573DWG	SOIC-20 (Pb-Free)	38 Units / Rail
MC74LCX573DWR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LCX573DTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74LCX573DTR2G	TSSOP-20 (Pb-Free)	2500 Tape & Reel
NLV74LCX573DTR2G*	TSSOP-20 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{1.} I_O absolute maximum rating must be observed.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°C	to +85°C	T _A = -55°C	to +125°C	
Symbol	Characteristic	Condition	Min	Max	Min	Max	Units
V _{IH}	HIGH Level Input	$2.3 \text{ V} \le \text{V}_{CC} \le 2.7 \text{ V}$	1.7		1.7		V
	Voltage (Note 2)	$2.7 \text{ V} \le \text{V}_{CC} \le 3.6 \text{ V}$	2.0		2.0		
V _{IL}	LOW Level Input	$2.3 \text{ V} \le \text{V}_{CC} \le 2.7 \text{ V}$		0.7		0.7	V
	Voltage (Note 2)	$2.7~\textrm{V} \leq \textrm{V}_{\textrm{CC}} \leq 3.6~\textrm{V}$		0.8		0.8	
V _{OH}	HIGH Level Out-	$2.3~V \le V_{CC} \le 3.6~V;~I_{OL} = 100~\mu A$	V _{CC} - 0.2		V _{CC} - 0.2		V
	put Voltage	$V_{CC} = 2.3 \text{ V}; I_{OH} = -8 \text{ mA}$	1.8		1.8		
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		2.2		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -18 \text{ mA}$	2.4		2.4		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -24 \text{ mA}$	2.2		2.2		
V _{OL}	DL LOW Level Output Voltage	$2.3~V \le V_{CC} \le 3.6~V;~I_{OL}$ = 100 μA		0.2		0.2	V
		$V_{CC} = 2.3 \text{ V}; I_{OL} = 8 \text{ mA}$		0.6		0.6	
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4		0.4	
		V _{CC} = 3.0 V; I _{OL} = 24 mA		0.55		0.60	
l _{OZ}	3-State Output Current	$V_{CC} = 3.6 \text{ V}, V_{IN} = V_{IH} \text{ or } V_{IL}, V_{OUT} = 0 \text{ to } 5.5 \text{ V}$		±5		±5	μΑ
l _{OFF}	Power Off Leak- age Current	$V_{CC} = 0$, $V_{IN} = 5.5 \text{ V or } V_{OUT} = 5.5 \text{ V}$		10		10	μА
I _{IN}	Input Leakage Current	V_{CC} = 3.6 V, V_{IN} = 5.5 V or GND		±5		±5	μΑ
I _{CC}	Quiescent Supply Current	V_{CC} = 3.6 V, V_{IN} = 5.5 V or GND		10		10	μΑ
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \leq V_{CC} \leq 3.6$ V; V_{IH} = V_{CC} – 0.6 V		500		500	μΑ

^{2.} These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS $t_R = t_F = 2.5 \text{ ns}; R_L = 500 \ \Omega$

					Lir	nits			
					T _A = -55°C	to +125°C			
			V _{CC} = 3.3	3 V ± 0.3 V	V _{CC} =	= 2.7 V	V _{CC} = 2.5	5 V ± 0.2 V	
			C _L =	50 pF	C _L =	50 pF	C _L =	30 pF	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Units
t _{PLH} t _{PHL}	Propagation Delay D _n to O _n	1	1.5 1.5	8.0 8.0	1.5 1.5	9.0 9.0	1.5 1.5	9.6 9.6	ns
t _{PLH} t _{PHL}	Propagation Delay LE to O _n	3	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	1.5 1.5	10.5 10.5	ns
t _{PZH} t _{PZL}	Output Enable Time to HIGH and LOW Level	2	1.5 1.5	8.5 8.5	1.5 1.5	9.5 9.5	1.5 1.5	10.5 10.5	ns
t _{PHZ} t _{PLZ}	Output Disable Time From High and Low Level	2	1.5 1.5	6.5 6.5	1.5 1.5	7.0 7.0	1.5 1.5	7.8 7.8	ns
t _s	Setup Time, HIGH or LOW D _n to LE	3	2.5		2.5		4.0		
t _h	Hold Time, HIGH or LOW D _n to LE	3	1.5		1.5		2.0		
t _w	LE Pulse Width, HIGH	3	3.3		3.3		4.0		
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 3)			1.0 1.0					ns

^{3.} Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

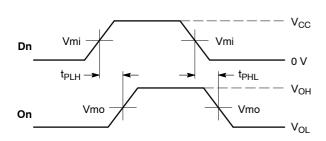
DYNAMIC SWITCHING CHARACTERISTICS

			Т	A = +25°C		
Symbol	Characteristic	Condition	Min	Тур	Max	Units
V _{OLP}	Dynamic LOW Peak Voltage (Note 4)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V V_{CC} = 2.5 V, C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V		0.8 0.6		V V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4)	$\begin{aligned} &V_{CC} = 3.3 \text{ V, } C_L = 50 \text{ pF, } V_{IH} = 3.3 \text{ V, } V_{IL} = 0 \text{ V} \\ &V_{CC} = 2.5 \text{ V, } C_L = 30 \text{ pF, } V_{IH} = 2.5 \text{ V, } V_{IL} = 0 \text{ V} \end{aligned}$		-0.8 -0.6		V

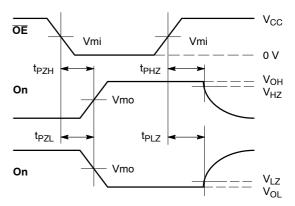
^{4.} Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

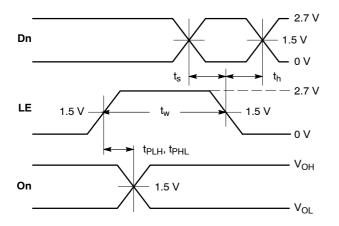
Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	7	pF
C _{I/O}	Input/Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10 MHz, V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	25	pF



WAVEFORM 1 – PROPAGATION DELAYS $t_B = t_F = 2.5 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.5 \text{ ns}$, 10% to 90%; f = 1 MHz; $t_W = 500 \text{ ns}$

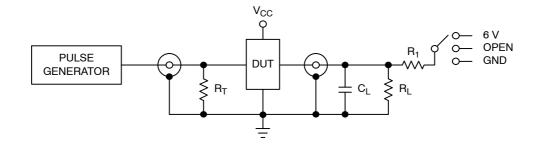


	V _{CC}				
Symbol	3.3 V \pm 0.3 V	2.7 V	2.5 V \pm 0.2 V		
Vmi	1.5 V	1.5 V	V _{CC} /2		
Vmo	1.5 V	1.5 V	V _{CC} /2		
V_{HZ}	V _{OL} + 0.3 V	V _{OL} + 0.3 V	V _{OL} + 0.15 V		
V_{LZ}	V _{OL} – 0.3 V	V _{OL} – 0.3 V	V _{OL} – 0.15 V		

WAVEFORM 3 – LE to On PROPAGATION DELAYS, LE MINIMUM PULSE WIDTH, Dn to LE SETUP AND HOLD TIMES

 t_R = t_F = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns except when noted

Figure 3. AC Waveforms



Test	Switch
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6 V at V $_{CC}$ = 3.3 \pm 0.3 V 6 V at V $_{CC}$ = 2.5 \pm 0.2 V
Open Collector/Drain t _{PLH} and t _{PHL}	6 V
t _{PZH} , t _{PHZ}	GND

Figure 4. Test Circuit

 $C_L=50$ pF at $V_{CC}=3.3\pm0.3$ V or equivalent (includes jig and probe capacitance) $C_L=30$ pF at $V_{CC}=2.5\pm0.2$ V or equivalent (includes jig and probe capacitance) $R_L=R_1=500$ Ω or equivalent $R_T=Z_{OUT}$ of pulse generator (typically 50 Ω)

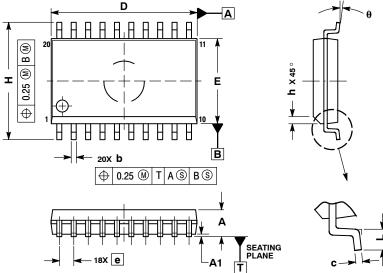




SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015

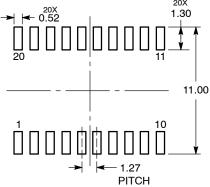
SCALE 1:1



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

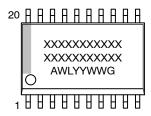
	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
b	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
A	0 °	7 °		

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASB42343B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-20 WB		PAGE 1 OF 1	

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

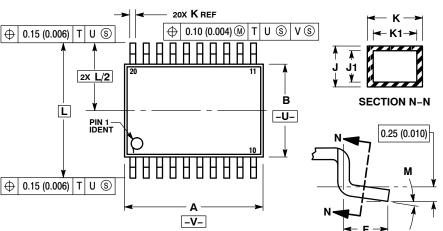
0.100 (0.004)

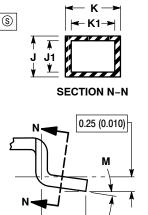
-T- SEATING

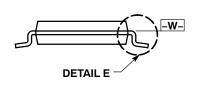


TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016







DETAIL E

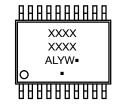
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION.
 SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Ĺ	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

◀	7.06
1	
	PITCH
16X 0.36 126	─
0.36 -	DIMENSIONS: MILLIMETERS

SOLDERING FOOTPRINT

DOCUMENT NUMBER:	98ASH70169A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP-20 WB		PAGE 1 OF 1	

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMi., and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer p

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative